

ABSTRACT

Please rewrite the Abstract as follows:

A semiconductor laser device having two active-layer stripe structures includes an n-InP substrate, an n-InP clad layer, a lower GRIN-SCH layer, an active layer, an upper GRIN-SCH layer, a p-InP clad layer, and a p-InGaAsP contact layer grown in this order, in a side cross section cut along one of the stripe structure. A high-reflection film is disposed on a reflection-side end surface, and a low-reflection film is disposed on an emission-side end surface. A p-side electrode is disposed on only a part of the upper surface of the p-InGaAsP contact layer so that a current non-injection area is formed on an area absent the p-side electrode.